

Absolute maximum ratings

($T_a=25^\circ\text{C}$)

Symbol	Ratings	Unit
V_{CB0}	200	V
V_{CEO}	200	V
V_{EBO}	6	V
I_c	3	A
I_{CP}	6 ($PW \leq 10\text{ms}$, $D_u \leq 50\%$)	A
I_B	0.2	A
I_F	3 ($PW \leq 0.5\text{ms}$, $D_u \leq 25\%$)	A
I_{FSM}	6 ($PW \leq 10\text{ms}$, single)	A
V_R	200	V
P_T	5 ($T_a=25^\circ\text{C}$) 25 ($T_c=25^\circ\text{C}$)	W
T_j	150	$^\circ\text{C}$
T_{stg}	-40 to +150	$^\circ\text{C}$

Electrical characteristics

($T_a=25^\circ\text{C}$)

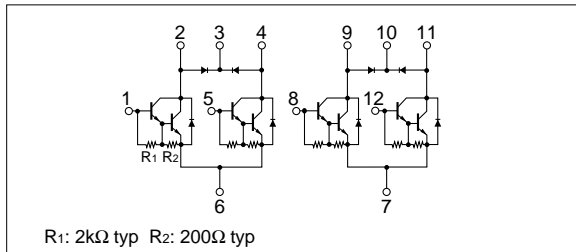
Symbol	Specification			Unit	Conditions
	min	typ	max		
I_{CB0}			10	μA	$V_{CB}=200\text{V}$
I_{EBO}			10	mA	$V_{EB}=6\text{V}$
V_{CEO}	200			V	$I_c=10\text{mA}$
h_{FE}	1000	6000	15000		$V_{CE}=4\text{V}$, $I_c=1.5\text{A}$
$V_{CE(sat)}$		1.1	1.5	V	$I_c=1.5\text{A}$, $I_b=3\text{mA}$
$V_{BE(sat)}$		1.7	2.0	V	
V_{FEC}			1.5	V	$I_{FEC}=2.0\text{A}$

Diode for flyback voltage absorption

($T_a=25^\circ\text{C}$)

Symbol	Specification			Unit	Conditions
	min	typ	max		
V_R	200			V	$I_R=10\mu\text{A}$
V_F			1.6	V	$I_F=1\text{A}$
I_R			10	μA	$V_R=200\text{V}$
t_{rr}		100		ns	$I_F=\pm 100\text{mA}$

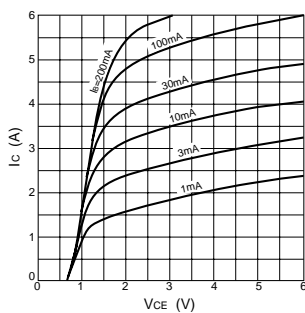
Equivalent circuit diagram



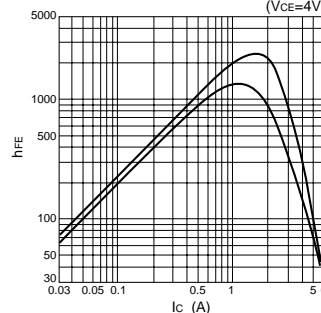
R1: 2k Ω typ R2: 200 Ω typ

Characteristic curves

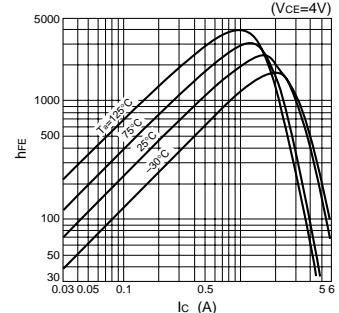
I_c - V_{CE} Characteristics (Typical)



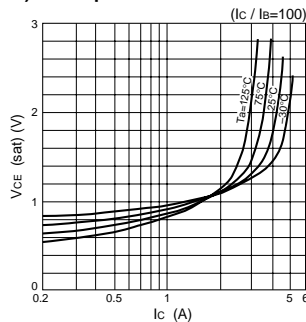
h_{FE} - I_c Characteristics (Typical)



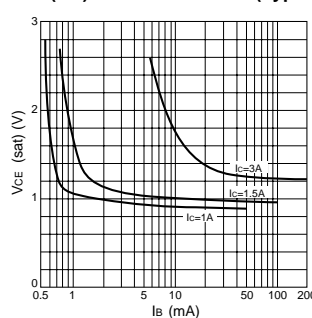
h_{FE} - I_c Temperature Characteristics (Typical)



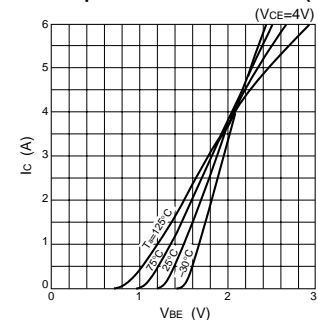
$V_{CE(sat)}$ - I_c Temperature Characteristics (Typical)



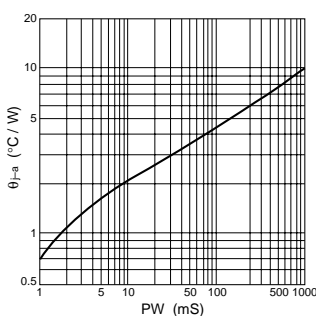
$V_{CE(sat)}$ - I_b Characteristics (Typical)



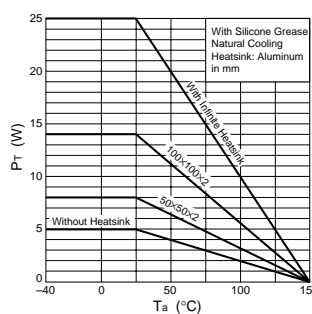
I_c - V_{BE} Temperature Characteristics (Typical)



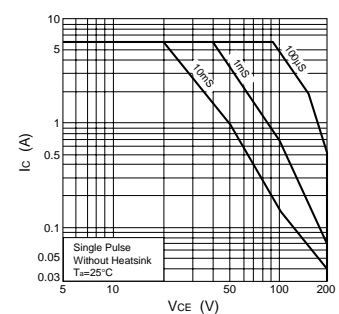
θ_{j-a} -PW Characteristics



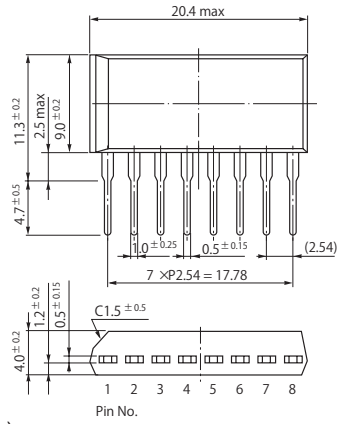
Pr- T_a Characteristics



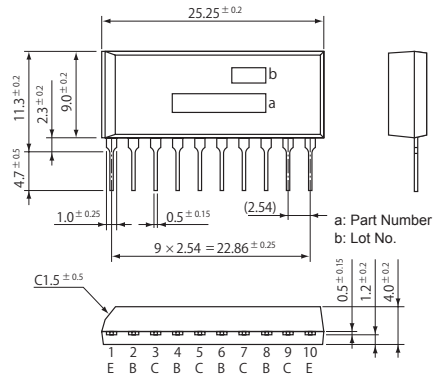
Safe Operating Area (SOA)



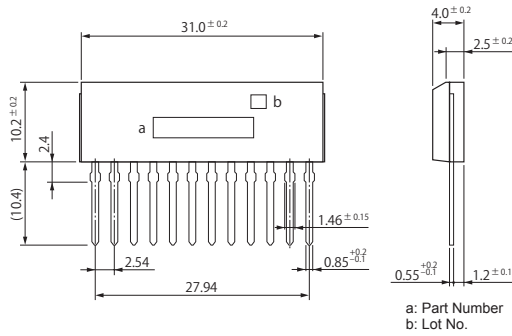
• SIP 8 (STA8Pin)



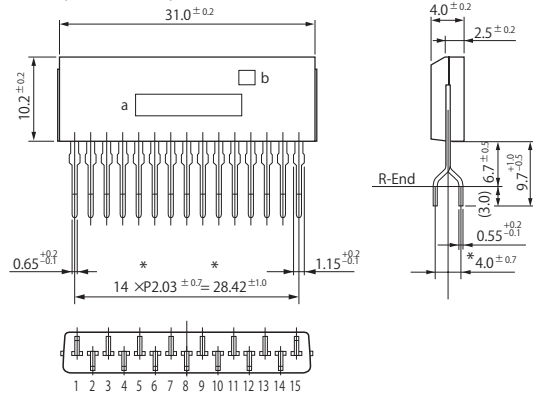
• SIP 10 (STA10Pin)



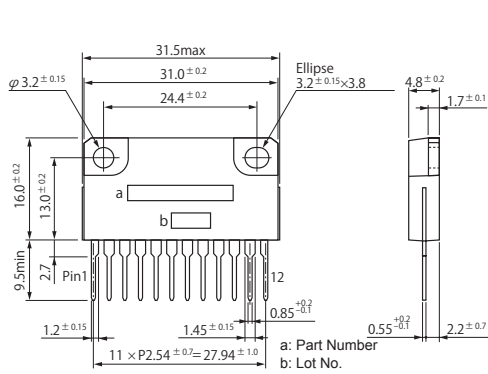
• SIP 12 (SMA12Pin)



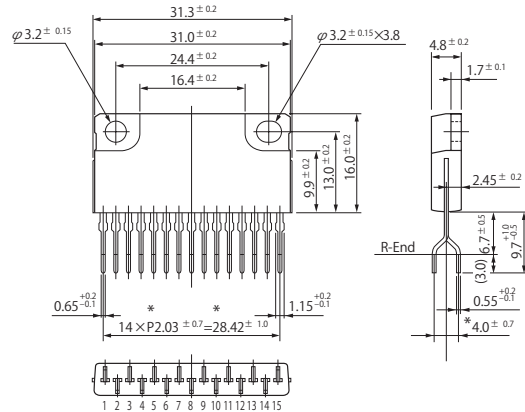
• SIP 15 (SMA15Pin)



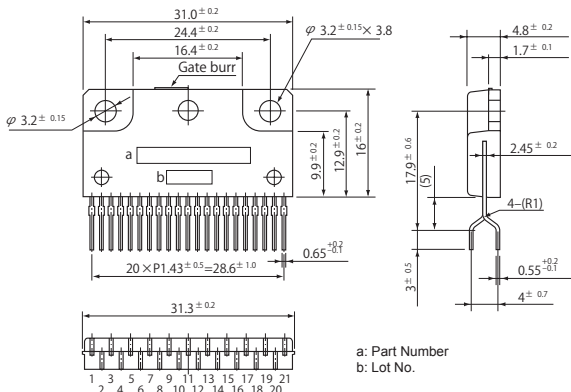
• SIP 12 with Fin (SLA12Pin)



• SIP 15 with Fin (SLA15Pin)



• SIP 21 with Fin (SLA21Pin)



(Unit:mm)